

METHOD OF FORMING TUNGSTEN FILM

Patent Number: JP2000178735
Publication date: 2000-06-27
Inventor(s): ISHIZUKA HODAKA; TACHIBANA MITSUHIRO
Applicant(s): TOKYO ELECTRON LTD
Requested Patent: JP2000178735
Application Number: JP19980375981 19981218
Priority Number(s):
IPC Classification: C23C16/08; H01L21/768
EC Classification:
Equivalents:

Abstract

PROBLEM TO BE SOLVED: To provide a method of forming a tungsten film to reduce the specific resistance of the film.
SOLUTION: When a tungsten film 50 is to be formed on the surface of the body W to be treated in a vacuum treating device, this method includes the following processes. The processes are, a seed crystal growing process to grow a tungsten seed crystal 48 on the surface of the body W in the presence of a film-forming gas containing a tungsten element, a boron exposing process to expose the treated body to an atmosphere of a gas containing boron in a short time after the first process, and a tungsten film forming process to grow the seed crystal to form a tungsten film in the presence of a film-forming gas containing a tungsten element. Thereby, the specific resistance of the tungsten film can be decreased.

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